

UTC UNISONIC TECHNOLOGIES CO., LTD

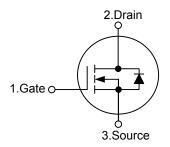
UT40N03T Power MOSFET

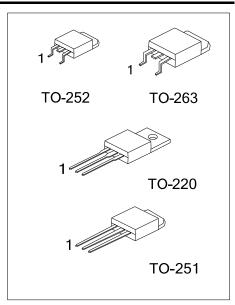
30V, 28A N-CHANNEL **ENHANCEMENT MODE** POWER MOSFET

FEATURES

- * $R_{DS(ON)}$ = 25m Ω @ V_{GS} = 10 V
- * Low capacitance
- * Optimized gate charge
- * Fast switching capability
- * Avalanche energy specified

SYMBOL

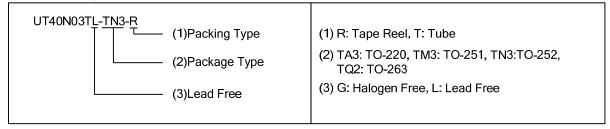




ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT40N03TL-TA3-T	UT40N03TG-TA3-T	TO-220	G	D	S	Tube	
UT40N03TL-TM3-R	UT40N03TG-TM3-R	TO-251	G	D	S	Tube	
UT40N03TL-TN3-R	UT40N03TG-TN3-R	TO-252	G	D	S	Tape Reel	
UT40N03TL-TN3-T	UT40N03TG-TN3-T	TO-252	G	D	S	Tube	
UT40N03TL-TQ2-R	UT40N03TG-TQ2-R	TO-263	G	D	S	Tape Reel	
UT40N03TL-TQ2-T	UT40N03TG-TQ2-T	TO-263	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	30	V	
Gate-Source Voltage		V_{GSS}	±25	V	
Continuous Drain Current		I _D	28	Α	
Pulsed Drain Current		I_{DM}	95	Α	
Total Dawer Dissipation	TO-220/TO-263	ם	45	14/	
Total Power Dissipation	TO-251/ TO-252	P_D	41	W	
Junction Temperature		T_J	+150	ç	
Storage Temperature		T_{STG}	-55 ~ + 150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
lunction to Ambient	TO-220/TO-263	0	62	°C/W	
Junction to Ambient	TO-251/ TO-252	θ_{JA}	100		
lunation to Casa	TO-220/TO-263	0	2.73	°C/W	
Junction to Case	TO-251/ TO-252	θ_{JC}	3	C/VV	

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

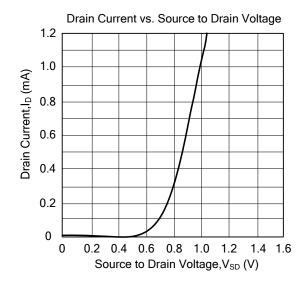
	1	+						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V		
Drain-Source Leakage Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V, T_{J} =25°C			1	μΑ		
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 25 \text{ V}$			±100	nA		
Breakdown Voltage Temperature Coefficient	Δ BV _{DSS} / Δ T _J	Reference to 25℃, I _D =1mA		0.032		V/°C		
ON CHARACTERISTICS								
Gate-Threshold Voltage	$V_{GS(TH)}$	V _{DS} =V _{GS} , I _D =250 μA			3	V		
Dunin Course On Otata Basistana	R _{DS(ON)}	V _{GS} =10 V, I _D =18 A			25	m0		
Drain-Source On-State Resistance		V_{GS} =4.5 V, I_{D} =14 A			45	mΩ		
DYNAMIC PARAMETERS								
Input Capacitance	C _{ISS}	\\ -25\\ \\ -0\\		655		pF		
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		145				
Reverse Transfer Capacitance	C _{RSS}	- I=1.UIVIH2		95]		
SWITCHING PARAMETERS								
Turn-ON Delay Time	t _{D(ON)}	40/// 45//		6		ns		
Turn-ON Rise Time	t _R	V _{GS} =10V,V _{DS} =15V,		62				
Turn-OFF Delay Time	t _{D(OFF)}	R_D =0.83 Ω , I_D =18 A, R_G =3.3 Ω		16				
Turn-OFF Fall-Time	t⊧	R _G -3.3 \(\Omega\)		4.4				
Total Gate Charge	Q_{G}	V 20V V 4.5V		8.8		nC		
Gate-Source Charge	Q _{GS}	V _{DS} =20V, V _{GS} =4.5V,		2.5				
Gate-Drain Charge	Q_{GD}	I _D =18A		5.8				
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward Voltage	V _{SD}	I _S =28 A, V _{GS} =0V			1.3	V		
Maximum Continuous Drain-Source Diode		\/ -\/ -0\/ \/ -1.2\/			20	^		
Forward Current	Is	$V_D=V_G=0V$, $V_S=1.3V$			28	Α		
Maximum Pulsed Drain-Source Diode	la				95	^		
Forward Current	I _{SM}				90	Α		

Notes: 1. Pulse width limited by $T_{J(MAX)}$.

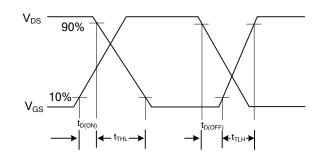
2. Pulse width ≤ 300us, duty cycle ≤ 2%.

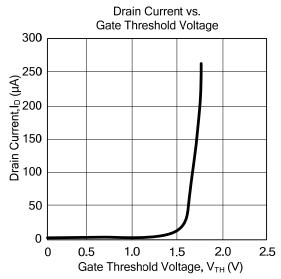
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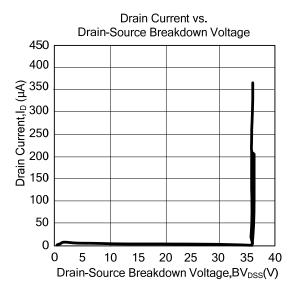
■ TYPICAL CHARACTERISTICS

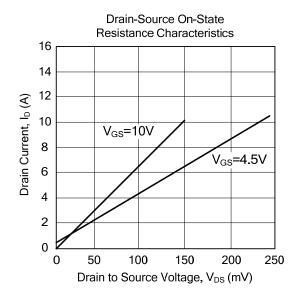


Switching Time Waveforms









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